

8kV 500mA HIGH VOLTAGE DIODE

GE-FOB is high reliability resin molded type high voltage diode in small size package which is sealed a multilayered mesa type silicon chip by epoxy resin.

Features

- High speed switching
- Low VF
- High surge resistivity for CRT discharge
- High reliability design
- Ultra small package

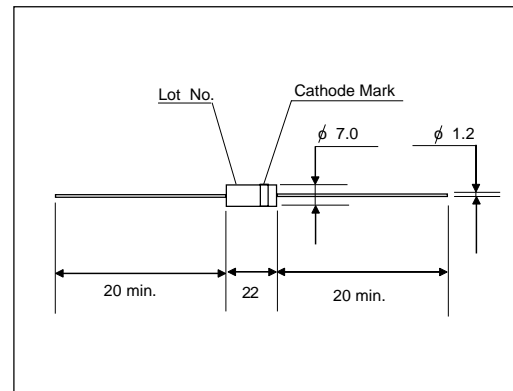
Applications

- X light Power supply
- Laser
- Voltage doubler circuit
- Microwave emission power

Maximum Ratings and Characteristics

- Absolute Maximum Ratings

Outline Drawings : mm



Cathode Mark

Type	Mark
GT-FOB	

Items	Symbols	Condition	GT-FOB	Units
Repetitive Peak Reverse Voltage	V_{RRM}		8	kV
Average Output Current	I_o	Ta=25°C, Resistive Load	500	mA
Surge Current	I_{FSM}		30	A _{peak}
Junction Temperature	T _J		155	°C
Allowable Operation Case Temperature	T _c		125	°C
Storage Temperature	T _{stg}		-40 to +155	°C

Electrical Characteristics (Ta=25°C Unless otherwise specified)

Items	Symbols	Conditions	GT-FOB	Units
Maximum Forward Voltage Drop	V_F	at 25°C, $I_F=I_{F(AV)}$	14	V
Maximum Reverse Current	IR1	at 25°C, $V_R=V_{RRM}$	1.0	μA
	IR2	at 100°C, $V_R=V_{RRM}$	10	μA
Maximum Reverse Recovery Time	T _{rr}	at 25°C	50	nS
Junction Capacitance	C _j	at 25°C, $V_R=0V, f=1MHz$	-	pF